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March 2015

# FDMS0302S

## N-Channel PowerTrench® SyncFET™

### 30 V, 49 A, 1.9 mΩ

## Features

- Max $r_{DS(on)}$ = 1.9 mΩ at $V_{GS}$ = 10 V, $I_D$ = 28 A
- Max $r_{DS(on)}$ = 2.4 mΩ at $V_{GS}$ = 4.5 V, $I_D$ = 23 A
- Advanced Package and Silicon Combination for Low $r_{DS(on)}$ and High Efficiency
- SyncFET Schottky Body Diode
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

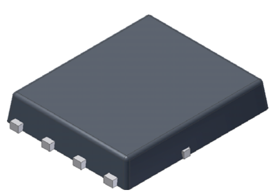
## General Description

The FDMS0302S has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.

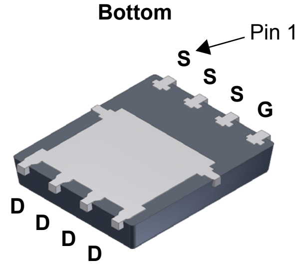
## Applications

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU Low Side Switch
- Networking Point of Load Low Side Switch

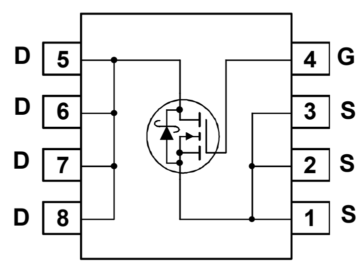
Top



Bottom




Power 56




## MOSFET Maximum Ratings $T_A$ = 25 °C unless otherwise noted.

| Symbol | Parameter | Ratings | Units |
|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | 30 | V |
| $V_{GS}$ | Gate to Source Voltage (Note 4) | ±20 | V |
| $I_D$ | Drain Current -Continuous (Package limited) $T_C$ = 25 °C | 49 | A |
| | -Continuous (Silicon limited) $T_C$ = 25 °C | 177 | |
| | -Continuous $T_A$ = 25 °C (Note 1a) | 29 | |
| | -Pulsed | 150 | |
| $E_{AS}$ | Single Pulse Avalanche Energy (Note 3) | 162 | mJ |
| $P_D$ | Power Dissipation $T_C$ = 25 °C | 89 | W |
| | Power Dissipation $T_A$ = 25 °C (Note 1a) | 2.5 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

### Thermal Characteristics

| | | | |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 1.4 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 50 | |

### Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDMS0302S | FDMS0302S | Power 56 | 13 ” | 12 mm | 3000 units |

## Electrical Characteristics $T_J$ = 25 °C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|

### Off Characteristics

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 1 mA, $V_{GS}$ = 0 V | 30 | | | V |
| $BV_{DSSt}$ | Drain to Source Breakdown Voltage (transient) | $V_{GS}$ = 0 V, $I_{D(aval)}$ = 8.6 A, $T_{case}$ = 25 °C, $t_{transient}$ = 10 ns | 34 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 10 mA, referenced to 25 °C | | 23 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 24 V, $V_{GS}$ = 0 V | | | 500 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current, Forward | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | | | 100 | nA |

### On Characteristics (Note 2)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}$, $I_D$ = 1 mA | 1.2 | 1.7 | 3.0 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 10 mA, referenced to 25 °C | | -5 | | mV/°C |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS}$ = 10 V, $I_D$ = 28 A | | 1.5 | 1.9 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 23 A | | 1.9 | 2.4 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 28 A, $T_J$ = 125 °C | | 2.0 | 2.6 | |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 5 V, $I_D$ = 28 A | | 181 | | S |

### Dynamic Characteristics

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz | | 5525 | 7350 | pF |
| $C_{oss}$ | Output Capacitance | | | 2020 | 2685 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 150 | 230 | pF |
| $R_g$ | Gate Resistance | | | 0.4 | 0.9 | Ω |

### Switching Characteristics

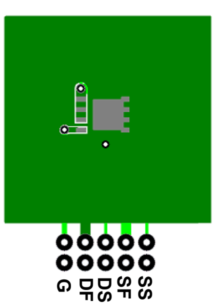
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 15 V, $I_D$ = 28 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | 20 | 36 | ns |
| $t_r$ | Rise Time | | | 8 | 17 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 43 | 70 | ns |
| $t_f$ | Fall Time | | | 5 | 10 | ns |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 10 V; $V_{DD}$ = 15 V, $I_D$ = 28 A | | 78 | 109 | nC |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 4.5 V; $V_{DD}$ = 15 V, $I_D$ = 28 A | | 35 | 49 | nC |
| $Q_{gs}$ | Gate to Source Gate Charge | $V_{DD}$ = 15 V, $I_D$ = 28 A | | 16.4 | | nC |
| $Q_{gd}$ | Gate to Drain "Miller" Charge | | | 6.6 | | nC |

### Drain-Source Diode Characteristics

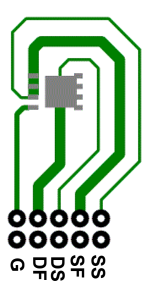
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 2 A (Note 2) | | 0.38 | 0.7 | V |
| | | $V_{GS}$ = 0 V, $I_S$ = 28 A (Note 2) | | 0.74 | 1.2 | |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 28 A, di/dt = 300 A/μs | | 46 | 75 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | 73 | 117 | nC |

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in$^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.




a. 50 °C/W when mounted on a 1 in$^2$ pad of 2 oz copper.




b.125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. $E_{AS}$ of 162 mJ is based on starting $T_J$ = 25 °C, L = 1 mH, $I_{AS}$ = 18 A, $V_{DD}$ = 27 V, $V_{GS}$ = 10 V. 100% test at L = 0.3 mH, $I_{AS}$ = 28 A.
4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

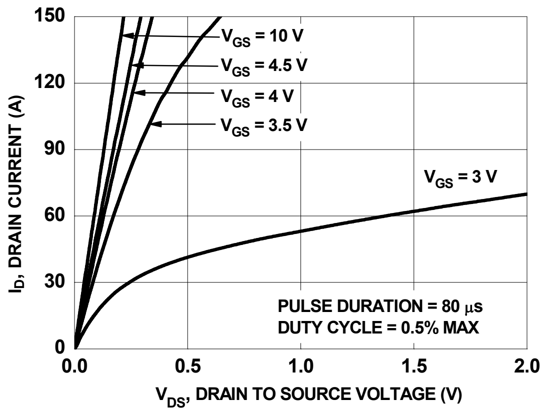



**Figure 1. On-Region Characteristics**

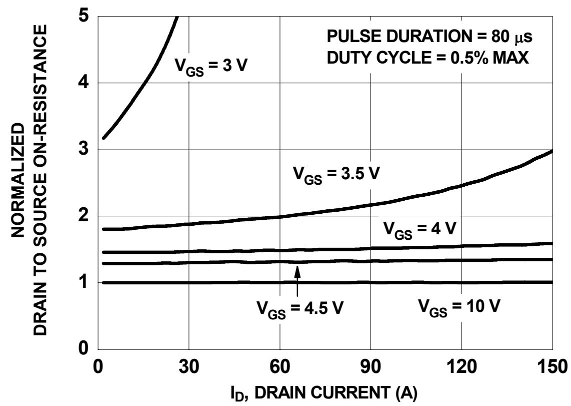



**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**

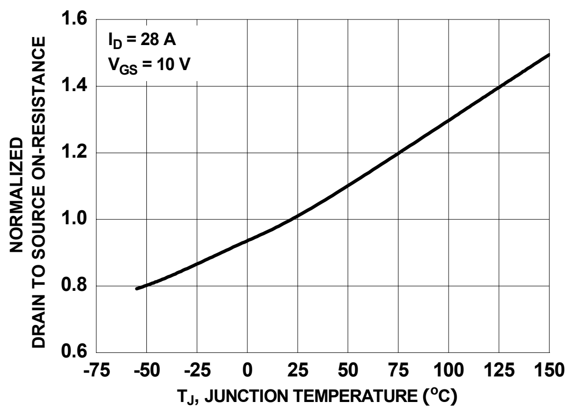



**Figure 3. Normalized On-Resistance vs. Junction Temperature**

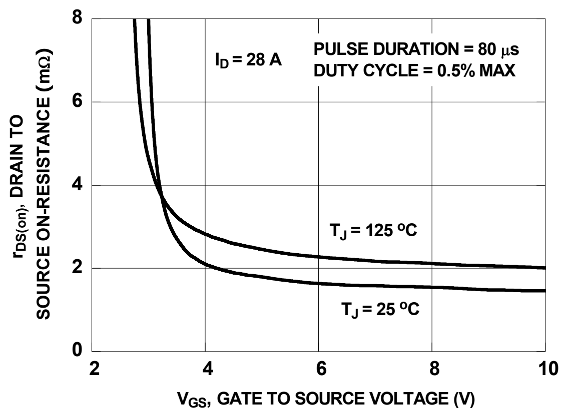



**Figure 4. On-Resistance vs. Gate to Source Voltage**

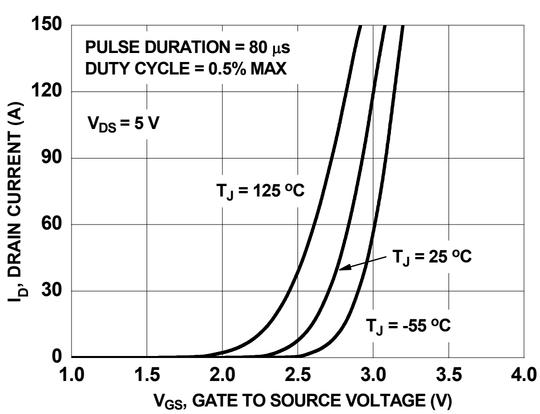



**Figure 5. Transfer Characteristics**

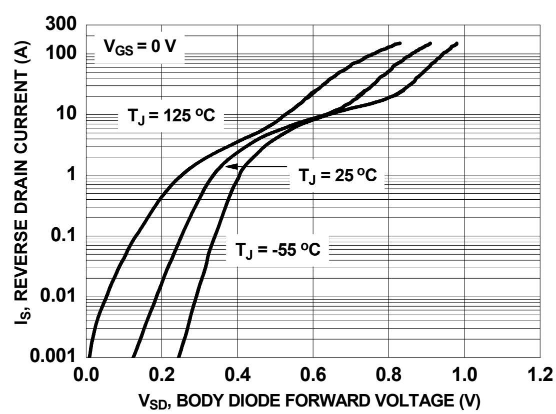



**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

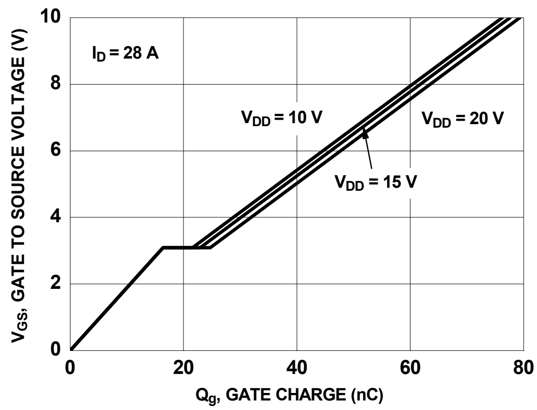



**Figure 7. Gate Charge Characteristics**

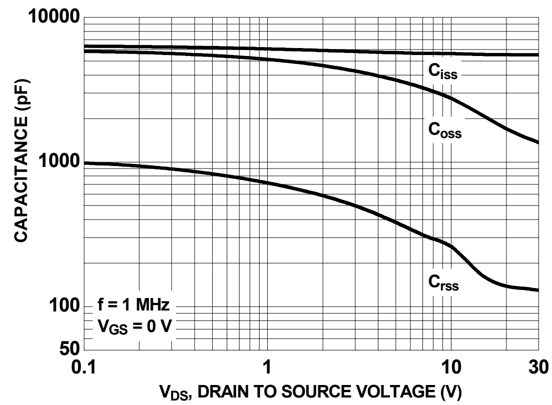



**Figure 8. Capacitance vs. Drain to Source Voltage**

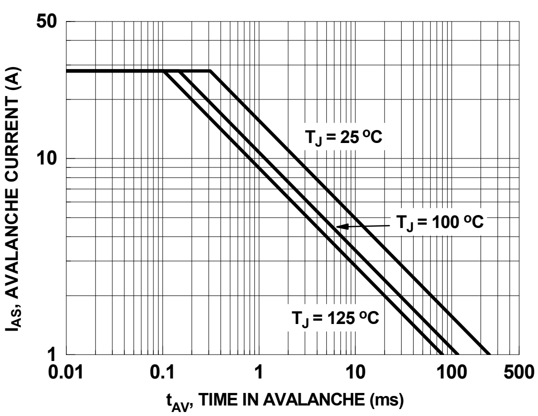



**Figure 9. Unclamped Inductive Switching Capability**

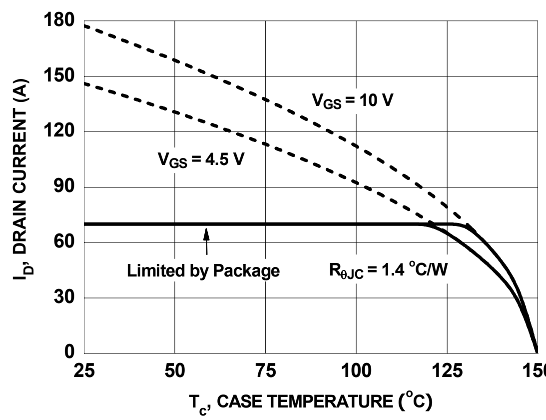



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

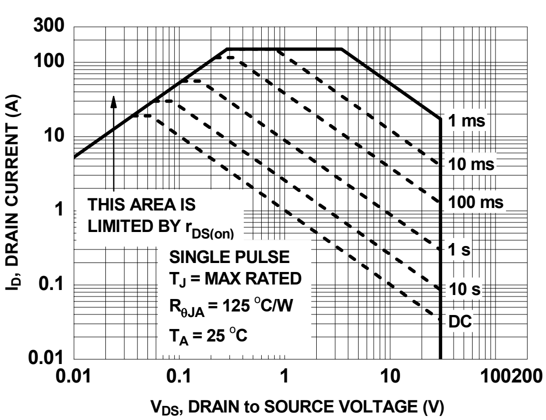



**Figure 11. Forward Bias Safe Operating Area**

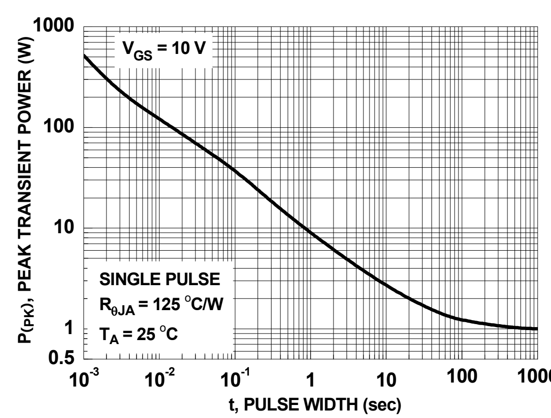



**Figure 12. Single Pulse Maximum Power Dissipation**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

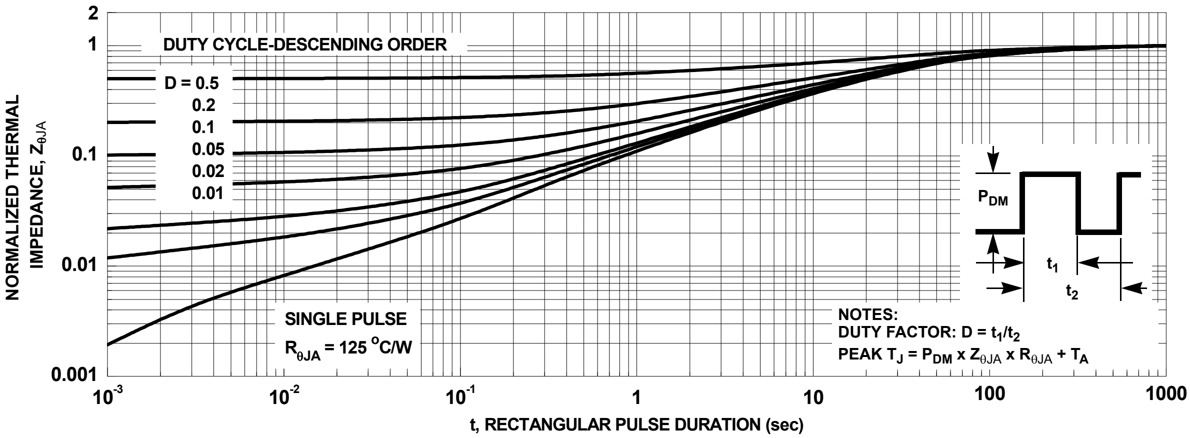



**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**

## Typical Characteristics (continued)

### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MoSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverses recovery characteristic of the FDMS0302S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

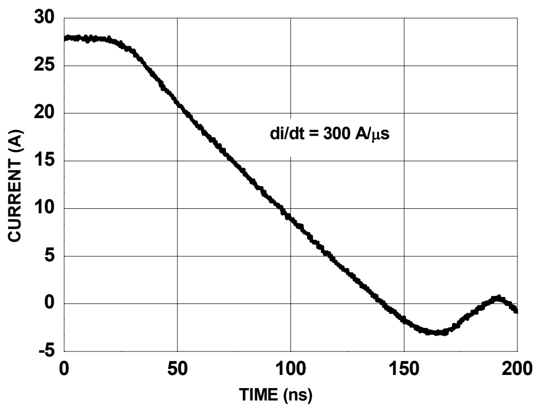



**Figure 14. FDMS0302S SyncFET Body Diode Reverse Recovery Characteristic**

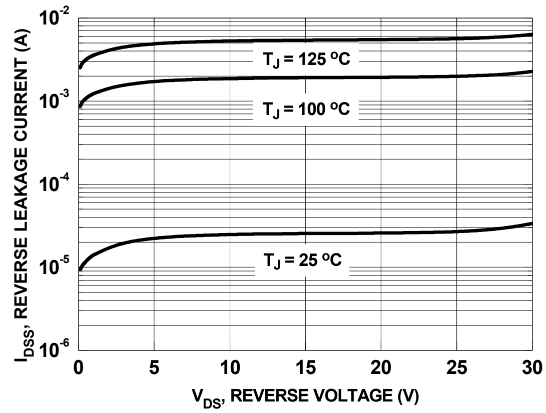
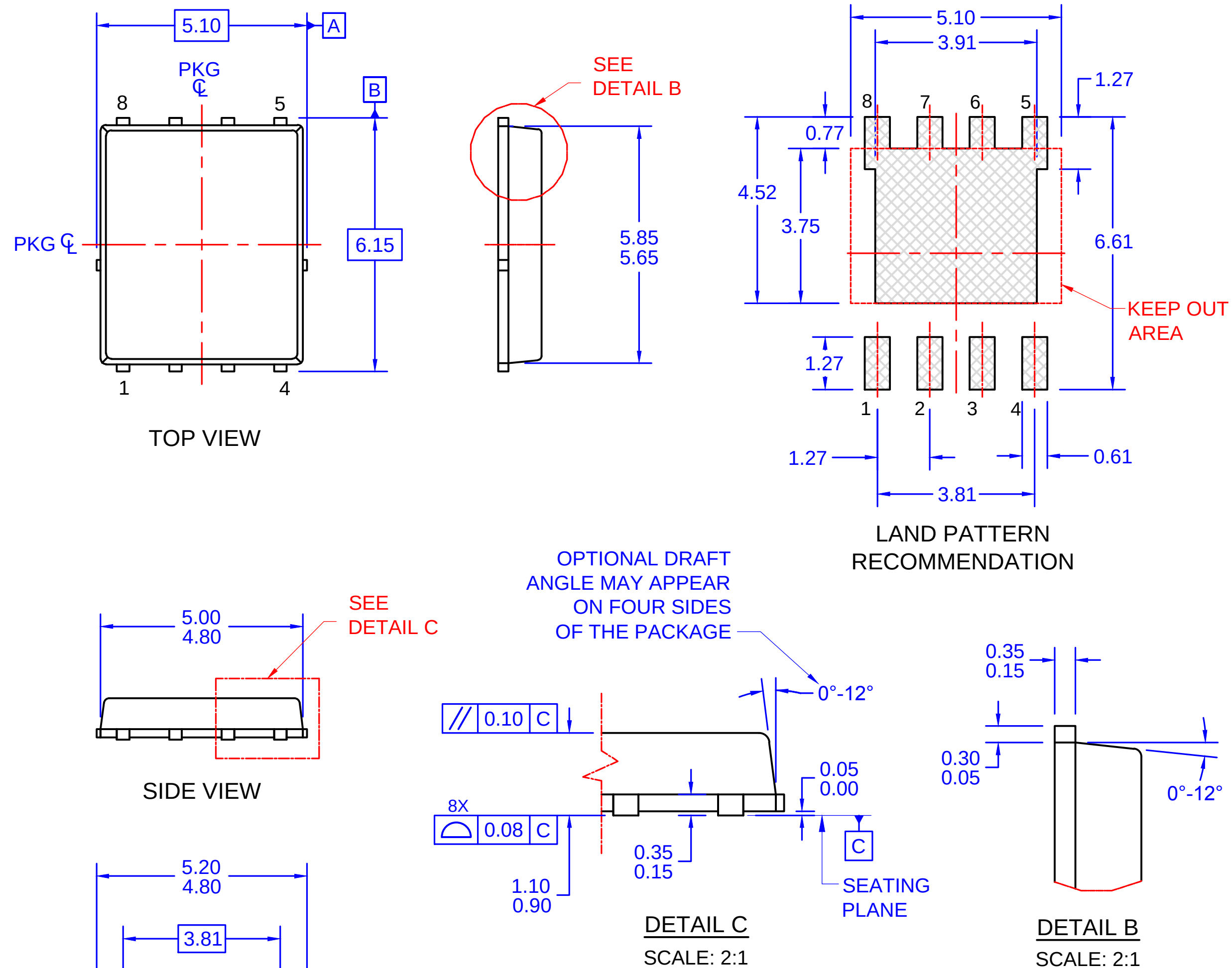
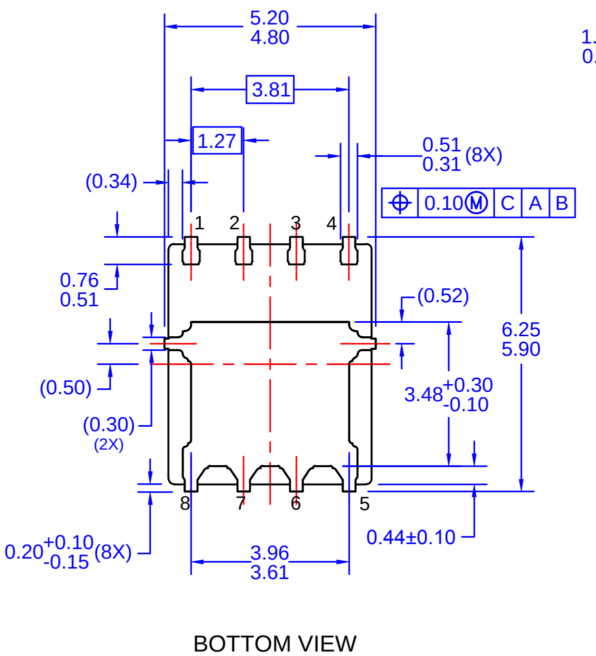



**Figure 15. SyncFET Body Diode Reverses Leakage vs. Drain-Source Voltage**

PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A




NOTES: UNLESS OTHERWISE SPECIFIED

A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,.
B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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